前言

在理想二极管防止电流倒灌和反接代替肖特基的应用中，比如在两个输入电压 Vin1 和 Vin2 的场景中，需要两个防止电流倒灌的理想二极管，在充电口和电池供电的场景中也是需要两个理想二极管，为了节省客户的产品空间和降低客户使用成本，MX5050S3028A2 是一款两通道的集成了功率 N-MOSFET 的理想二极管，该款产品能有效的降低通过该路的电源电压下降和功率损坏。

MX5050S3028A2 内部控制器产生一个内部的电荷泵开启集成的 N 通道 MOSFET， 内部集成了高速比较器，在输出电压比输入电压高 20mv 的时候能迅速的关掉内置的 N 通道 MOSFET，防止电流反向从输出倒灌到输入端。

MX5050S3028A2 输入电压范围是 4v 到 24v，能够承受最大瞬态电压 30v 的应用， 内置的 N-MOSFET 导通电阻是 28 毫欧，能够通最大 4A 的工作电流.

主要特征

♦ 比较宽的输入电压范围4v到24v

♦瞬态到30V的耐压能力

♦ 内置电荷泵，内置比较器根据MOSFET的压差调整电荷泵电压，精准绿色调整电荷泵电压控制MOSFET

♦ 高速比较器检测输出和输入压差，50ns关断MOS防止倒灌

♦用2A的峰值电流放电MOS的Gate-source 电压起到快速关断，防止倒灌关断的作用

♦SOP8封装，方便焊接

典型应用

12V 24V 系统的冗余电源应用

General information

订货信息

Part Number	Description
MX5050S3028A2	SOP8L
MPQ	3000pcs

Package dissipation rating

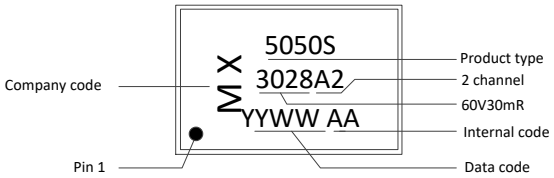
Package	RθJA（℃/W）
SOP8L	108.1

Absolute maximum ratings

Parameter	Value
IN, OUT Pins to GND	-0.3 to 30V
Internal MOSFET VDS	≥30V
Junction temperature	150℃
Storage temperature, Tstg	-50 to 150℃
Leading temperature （soldering,10secs）	260℃
ESD Susceptibility HBM	±2000V

以上是最大耐受参数，超过绝对最大额定值中列出的应力可能会对设备造成永久性损坏。长时间暴露在绝对最大额定值条件下可能会影响可靠性。不暗示设备在超出推荐作条件部分所示的任何条件下的功能运行。

标签信息



推荐工作条件

Symbol	Range
IN Pin	4-24V
Operating temperature	-40~125℃

General description

The MX5050S3028A2 high-side OR-ing works with an internal MOSFET and acts as an ideal diode rectifier when connected in series with the power supply. This OR-ing circuit enables MOSFETs to replace diode rectifiers in power distribution networks, reducing power loss and voltage drop.

The MX5050S3028A2 controller provides charge pump gate drive for an internal N-channel MOSFET and fast response comparator to turn off the FET when current flows in reverse.

The MX5050S3028A2 can be connected to power supplies from 4V to 24V and can withstand transient voltages up to 30V.

Features

- ♦ Wide operating input voltage range V_{IN}: 4V to 24V
- ♦30V transient voltage
- ♦ Charge pump gate driver for internal N-channel MOSFET
- ♦ 50ns fast response to current reversal
- ♦2A peak gate off current internal
- ♦Ultra-small V_{DS} turn-off voltage reduces turn-off time
- ♦ 8-Pin SOP8L

Applications

Active OR-ing of redundant (N+1) power supplies

General information

Ordering information

Part Number	Description
MX5050S3028A2	SOP8L
MPQ	3000pcs

Package dissipation rating

Package	RθJA（℃/W）
SOP8L	108.1

Absolute maximum ratings

Parameter	Value
IN, OUT Pins to GND	-0.3 to 30V
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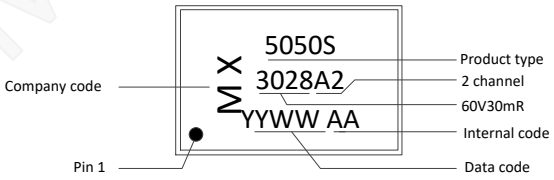
Leading temperature （soldering,10secs）	260℃
ESD Susceptibility HBM	±2000V

Stresses beyond those listed in Absolute Maximum Ratings may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect reliability. Functional operation of the device at any conditions beyond those indicated in the Recommended Operating Conditions section is not implied.

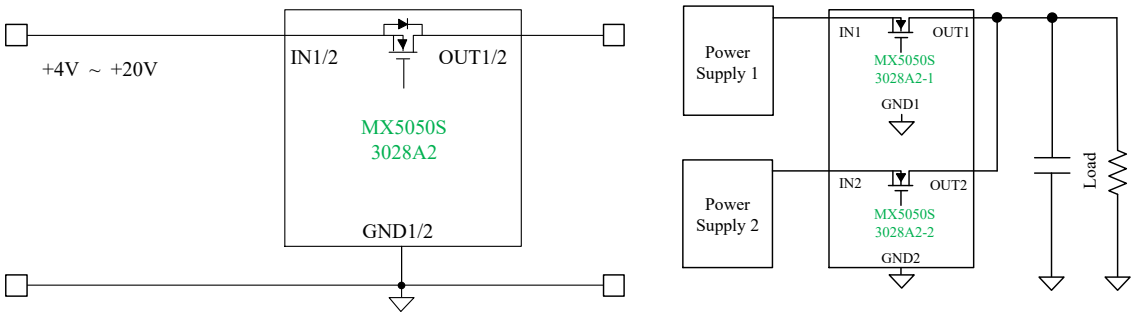
Marking information



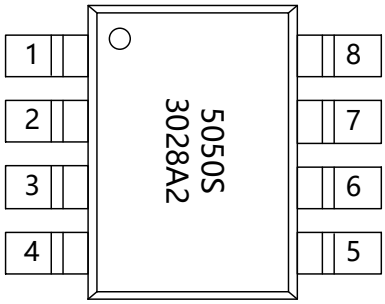
Recommended operating condition

Symbol	Range
IN Pin	4-24V
Operating temperature	-40~125℃

Typical application



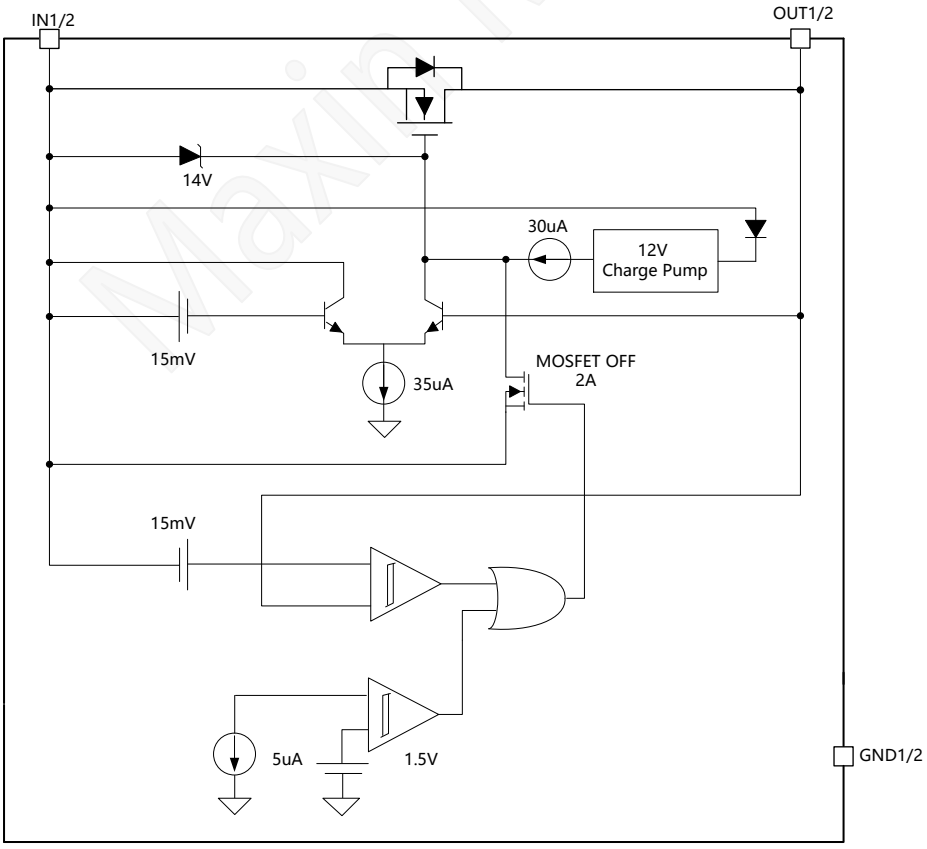
Terminal assignments



Pin information

PIN NO.	PIN name	Description
1	IN1	Voltage sense connection and power supply for channel 1.
2	GND1	Ground for the controller with channel 1.
3	IN2	Voltage sense connection and power supply for channel 2.
4	GND2	Ground for the controller with channel 2.
5、6	OUT2	Voltage sense connection to the OUTPUT for channel 2.
7、8	OUT1	Voltage sense connection to the OUTPUT for channel 1.

Block diagram



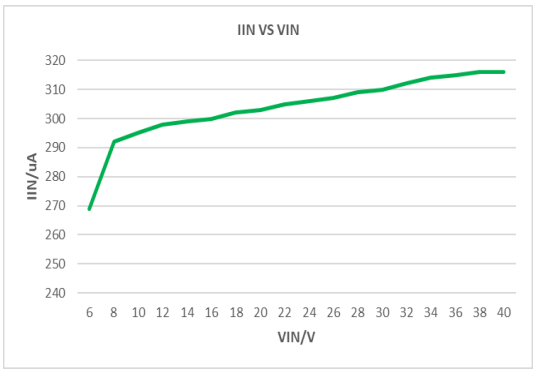
Electrical characteristics

（V_{IN} =12V, TA = 25℃, unless otherwise noted）

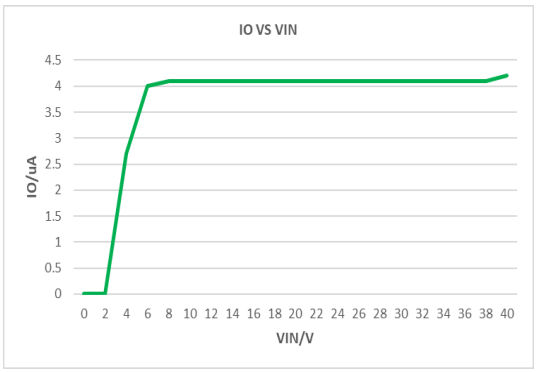
Symbol	Parameter	Test condition	Min	Typ.	Max	Unit
IN PIN						
V_{IN}	Operating Input Voltage Range		4		24	V
I_{IN}	IN Pin current	V_{IN} =5V	150	240	300	uA
		V_{IN} = 8V to 20V	200	300	400	
OUT PIN						
V_{OUT}	Operating Output Voltage Range		4		24	V
I_{OUT}	OUT Pin Current	V_{IN} = 4V to 20V		4.1		uA
INTERNAL REGULATOR						
$V_{SD(REV)}$	Reverse V_{SD} Threshold V_{IN} < V_{OUT}	V_{IN} - V_{OUT}	-35	–15	-5	mV
$V_{SD(REG)}$	Regulated Forward V_{SD} Threshold V_{IN} > V_{OUT}	V_{IN} = 5V, V_{IN} - V_{OUT}	1	30	40	mV
		V_{IN} = 12V, V_{IN} - V_{OUT}	5	60	80	
INTERNAL MOSFET						
V_{DS}	Drain to source voltage	I_{DS} = 250uA	30			V
R_{ON}	On resistance	I_D = 1A		28	35	mΩ

Characteristic plots

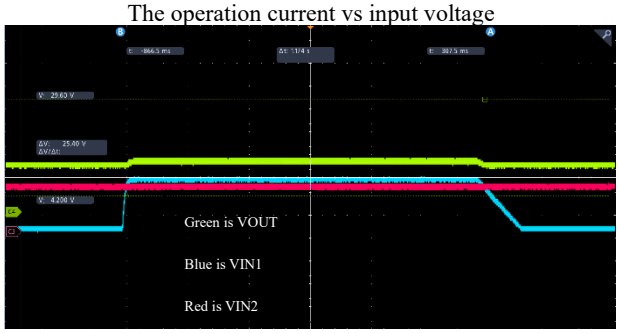
（V_{IN} = V_{OUT}, T_A = 25℃, unless otherwise noted）



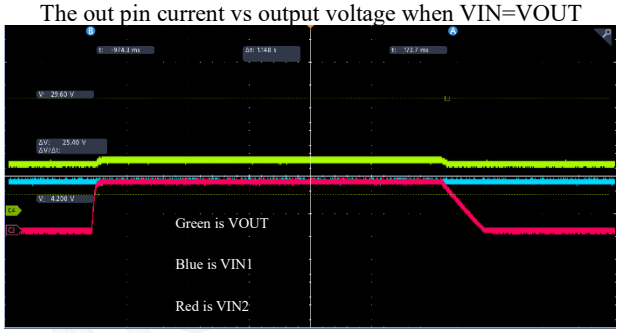
The operation current vs input voltage



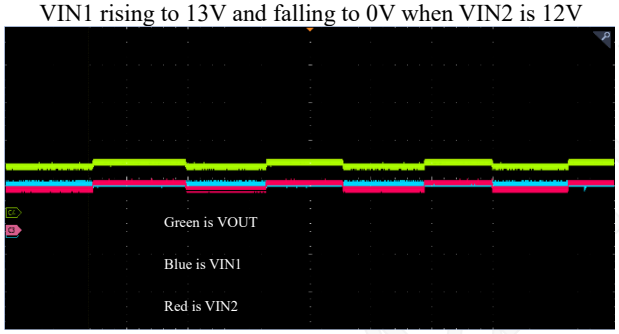
The out pin current vs output voltage when VIN=VOUT



VIN1 rising to 13V and falling to 0V when VIN2 is 12V



VIN2 rising to 13V and falling to 0V when VIN1 is 12V



VIN2 rising to 13V and falling to 11V when VIN2 is 12V

Operation description

IN and OUT Pins

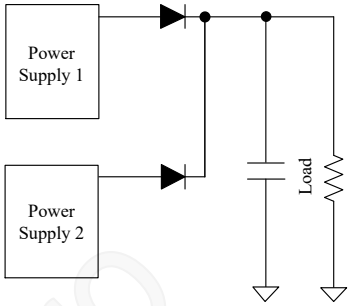
When power is initially applied, the load current will flow from source to drain through the body diode of the MOSFET. Once the voltage across the body diode exceeds $V_{SD(REG)}$ then the MX5050S3028A2 begins charging the internal MOSFET gate through a 30 µA (typical) charge pump current source. In forward operation, the gate of the internal MOSFET is charged. The MX5050S3028A2 is designed to regulate the internal MOSFET gate-to-source voltage. If the MOSFET current decreases to the point that the voltage across the MOSFET falls below the $V_{SD(REG)}$ voltage regulation point of 30mV (typical), the internal MOSFET gate voltage will be decreased until the voltage across the MOSFET is regulated at 30mV. If the source-to-drain voltage is greater than the $V_{SD(REG)}$ voltage, the gate-to-source voltage will increase and eventually reach the 12V gate to IN pin Zener clamp level.

If the MOSFET current reverses, possibly due to failure of the input supply, such that the voltage across the MX5050S3028A2 IN and OUT pins is more negative than the $V_{SD(REV)}$ voltage of -28mV (typical), the MX5050S3028A2 will quickly discharge the internal MOSFET gate through a strong gate to IN pin discharge transistor. If the input supply fails abruptly, as would occur if the supply was shorted directly to ground, a reverse current will temporarily flow through the MOSFET until the gate can be fully discharged. This reverse current is sourced from the load capacitance and from the parallel connected supplies. The MX5050S3028A2 responds to a voltage reversal condition typically within 50ns. The actual time required to turn off the MOSFET will depend on the charge held by the gate capacitance of the MOSFET being used. For MX5050S3028A2, the gate capacitance of the internal MOSFET is 4.6nF and the typical turn off time is 25ns. This fast turnoff time minimizes voltage disturbances at the output, as well as the current transients from the redundant supplies.

Application and Implementation

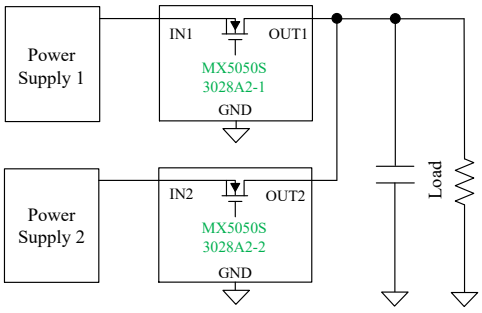
Application Information

Systems that require high availability often use multiple, parallel-connected redundant power supplies to improve reliability. Schottky OR-ing diodes are typically used to connect these redundant power supplies to a common point at the load. The disadvantage of using OR-ing diodes is the forward voltage drop, which reduces the available voltage and the associated power losses as load currents increase. Using an N-channel MOSFET to replace the OR-ing diode requires a small increase in the level of complexity, but reduces, or eliminates, the need for diode heat sinks or large thermal copper area in circuit board layouts for high power applications.



OR-ing with Diodes

The MX5050S3028A2 is a positive voltage (that is, high-side) OR-ing controller that will drive an external N-channel MOSFET to replace an OR-ing diode. The voltage across the MOSFET source and drain pins is monitored by the MX5050S3028A2 at the IN and OUT pins, while the internal MOSFET gate drives the MOSFET to control its operation based on the monitored source-drain voltage. The resulting behavior is that of an ideal rectifier with source and drain pins of the MOSFET acting as the anode and cathode pins of a diode respectively.



OR-ing with internal MOSFETs

Short Circuit Failure of an Input Supply

An abrupt 0Ω short circuit across the input supply will cause the highest possible reverse current to flow while the internal MX5050S3028A2 control circuitry discharges the gate of the MOSFET. During this time, the reverse current is limited only by the $R_{DS(ON)}$ of the MOSFET, along with parasitic wiring

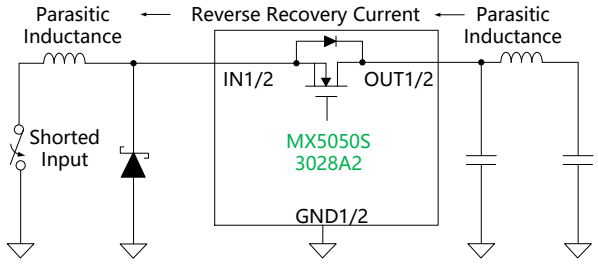
resistances and inductances. Worst case instantaneous reverse current would be limited to:

$I_{D(REV)} = (V_{OUT} - V_{IN}) / R_{DS(ON)}$ (1)

The internal Reverse Comparator will react, and will start the process of discharging the internal MOSFET gate, when the reverse current reaches:

$I_{D(REV)} = V_{SD(REV)} / R_{DS(ON)}$ (2)

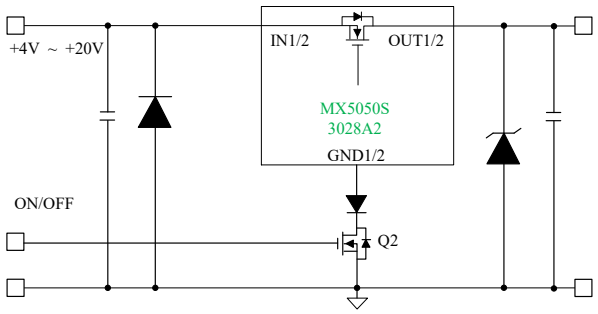
When the MOSFET is finally switched off, the energy stored in the parasitic wiring inductances will be transferred to the rest of the circuit. As a result, the MX5050S3028A2 IN pin will see a negative voltage spike while the OUT pin will see a positive voltage spike. The IN pin can be protected by diode clamping the pin to GND in the negative direction. The OUT pin can be protected with a TVS protection diode, a local bypass capacitor, or both.



Reverse Recovery Current Generates Spikes at V_{IN} and V_{OUT}

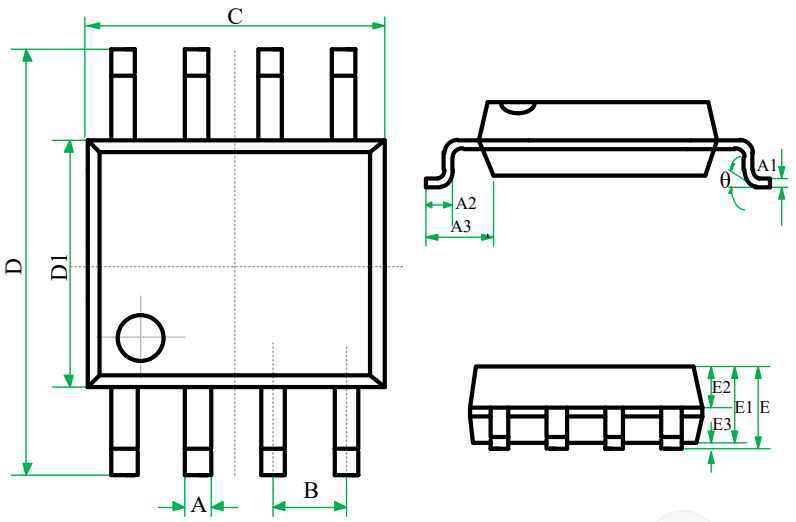
Reverse Input Voltage Protection with IQ Reduction

In battery powered applications, whenever MX5050S3028A2 functionality is not needed, the supply to the MX5050S3028A2 can be disconnected by turning off Q2, as shown in the following figure. This disconnects to the ground path of the MX5050S3028A2 and eliminates the current leakage from the battery.



Reverse input voltage protection with IQ reduction schematic

Package information



SYMBOL	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.39	-	0.48	0.0154	-	0.0189
A1	0.21	-	0.28	0.008	-	0.011
A2	0.50	-	0.80	0.020	-	0.031
A3	1.05BSC			0.041BSC		
B	1.27BSC			0.050BSC		
C	4.70	4.90	5.10	0.185	0.193	0.201
D	5.80	6.00	6.20	0.228	0.236	0.244
D1	3.70	3.90	4.10	0.146	0.154	0.161
E	-	-	1.75	-	-	0.069
E1	1.30	1.40	1.50	0.051	0.055	0.059
E2	0.60	0.65	0.70	0.024	0.026	0.028
E3	0.10	-	0.225	0.004	-	0.009
θ	0	-	8°	0	-	8°

SOP8 for MX5050S3028A2

Restrictions on Product Use

◆ MAXIN micro is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing MAXIN products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such MAXIN products could cause loss of human life, bodily injury or damage to property.

◆ In developing your designs, please ensure that MAXIN products are used within specified operating ranges as set forth in the most recent MAXIN products specifications.

◆ The information contained herein is subject to change without notice.

Version update record:

V10 The original version